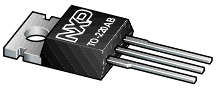


PSMN3R3-60PL

N-channel 60 V, 3.4 mΩ logic level MOSFET in SOT78

7 February 2013 Product data sheet

1. General description

Logic level N-channel MOSFET in SOT78 using TrenchMOS technology. Product design and manufacture has been optimized for use in battery operated power tools.

2. Features and benefits

- High efficiency due to low switching & conduction losses
- Robust construction for demanding applications
- Logic level gate

3. Applications

- Battery-powered tools
- Load switching
- Motor control
- Uninterruptible power supplies

4. Quick reference data

Table 1. Quick reference data

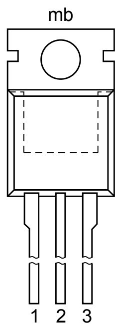
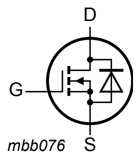
Symbol	Parameter	Conditions		Min	Typ	Max	Unit
V_{DS}	drain-source voltage	$T_j \geq 25$ °C; $T_j \leq 175$ °C		-	-	60	V
I_D	drain current	V_{GS} = 10 V; T_{mb} = 25 °C; Fig. 1	[1]	-	-	130	A
P_{tot}	total power dissipation	T_{mb} = 25 °C; Fig. 2		-	-	293	W
Static characteristics							
R_{DSon}	drain-source on-state resistance	V_{GS} = 10 V; I_D = 25 A; T_j = 25 °C; Fig. 11		-	2.7	3.4	mΩ
Dynamic characteristics							
$Q_{G(tot)}$	total gate charge	V_{GS} = 10 V; I_D = 25 A; V_{DS} = 48 V; Fig. 13; Fig. 14		-	175	-	nC
Q_{GD}	gate-drain charge			-	31	-	nC
Avalanche ruggedness							
$E_{DS(AL)S}$	non-repetitive drain-source avalanche energy	I_D = 130 A; $V_{sup} \leq 60$ V; R_{GS} = 50 Ω; V_{GS} = 10 V; $T_{j(init)}$ = 25 °C; unclamped; Fig. 3		-	-	372	mJ

[1] Continuous current is limited by package.

Scan or click this QR code to view the latest information for this product

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate	 **TO-220AB (SOT78)**	
2	D	drain		
3	S	source		

6. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
PSMN3R3-60PL	TO-220AB	plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB	SOT78

7. Marking

Table 4. Marking codes

Type number	Marking code
PSMN3R3-60PL	PSMN3R3-60PL

8. Limiting values

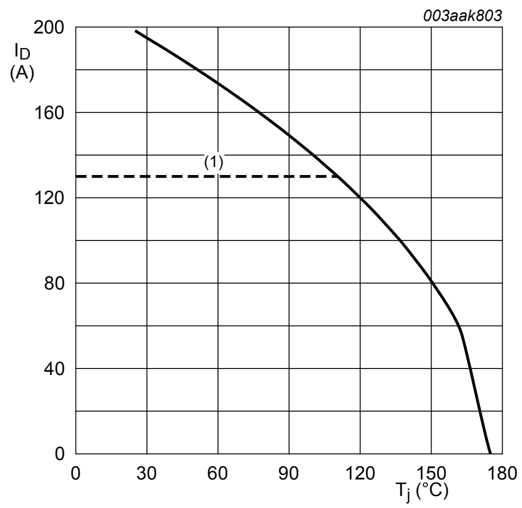
Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V_{DS}	drain-source voltage	$T_j \geq 25$ °C; $T_j \leq 175$ °C		-	60	V
V_{DGR}	drain-gate voltage	$R_{GS} = 20$ kΩ		-	60	V
V_{GS}	gate-source voltage			-20	20	V
I_D	drain current	$T_{mb} = 25$ °C; $V_{GS} = 10$ V; Fig. 1	[1]	-	130	A
		$T_{mb} = 100$ °C; $V_{GS} = 10$ V; Fig. 1	[1]	-	130	A
I_{DM}	peak drain current	$T_{mb} = 25$ °C; pulsed; $t_p \leq 10$ μs; Fig. 4		-	793	A

Symbol	Parameter	Conditions		Min	Max	Unit
P_{tot}	total power dissipation	T_{mb} = 25 °C; Fig. 2		-	293	W
T_{stg}	storage temperature			-55	175	°C
T_j	junction temperature			-55	175	°C
Source-drain diode						
I_S	source current	T_{mb} = 25 °C	[1]	-	130	A
I_{SM}	peak source current	pulsed; t_p ≤ 10 µs; T_{mb} = 25 °C		-	793	A
Avalanche ruggedness						
$E_{DS(AL)S}$	non-repetitive drain-source avalanche energy	I_D = 130 A; V_{sup} ≤ 60 V; R_{GS} = 50 Ω; V_{GS} = 10 V; $T_{j(init)}$ = 25 °C; unclamped; Fig. 3		-	372	mJ

[1] Continuous current is limited by package.



(1) Capped at 130A due to package

Fig. 1. Continuous drain current as a function of mounting base temperature

$$V_{GS} \geq 10V$$

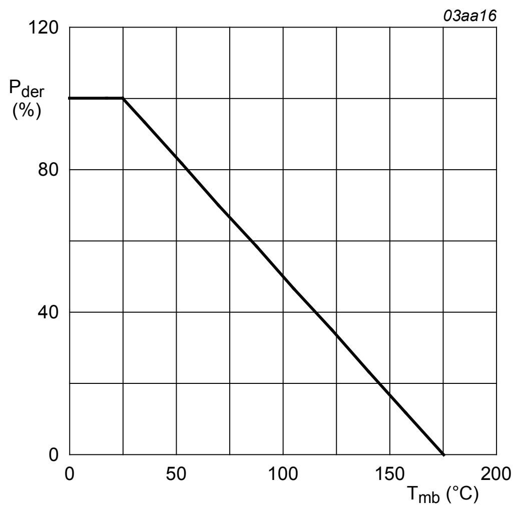


Fig. 2. Normalized total power dissipation as a function of mounting base temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25^\circ C)}} \times 100\,\%$$

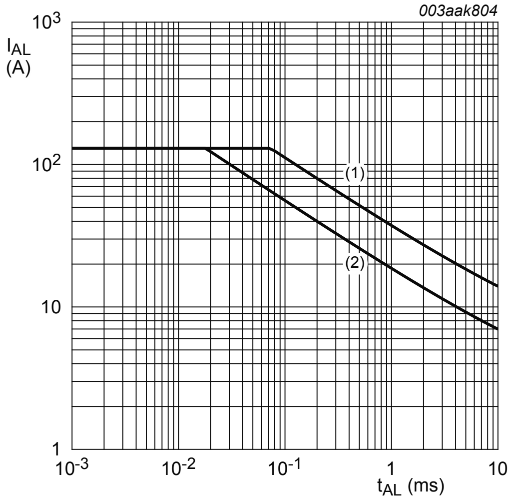


Fig. 3. Avalanche rating; avalanche current as a function of avalanche time

(1) $T_{j\ (init)} = 25°C$; (2) $T_{j\ (init)} = 100°C$

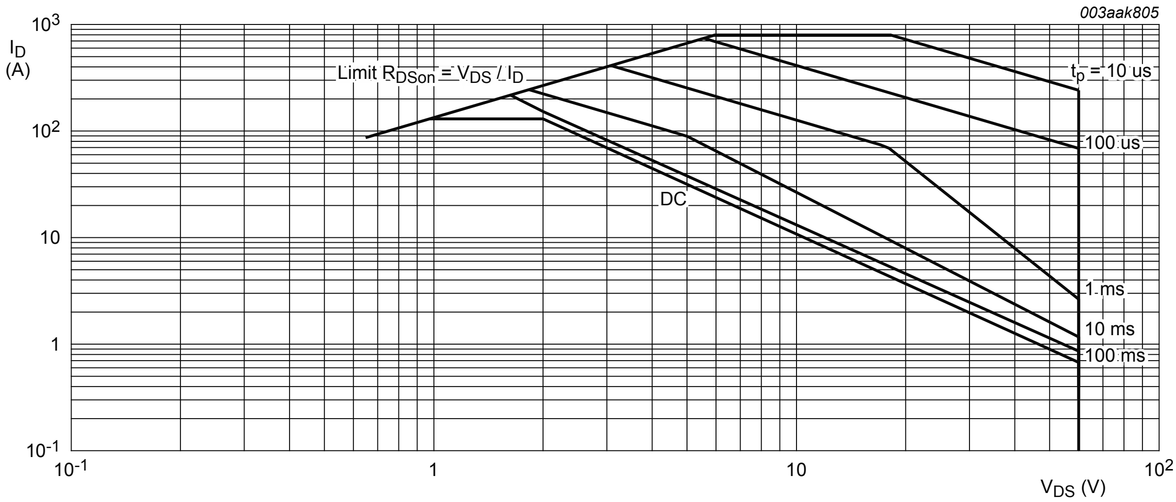


Fig. 4. Safe operating area; continuous and peak drain currents as a function of drain-source voltage

$T_{mb} = 25°C$; I_{DM} is a single pulse

9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	Fig. 5		-	0.4	0.51	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient	vertical in still air		-	60	-	K/W

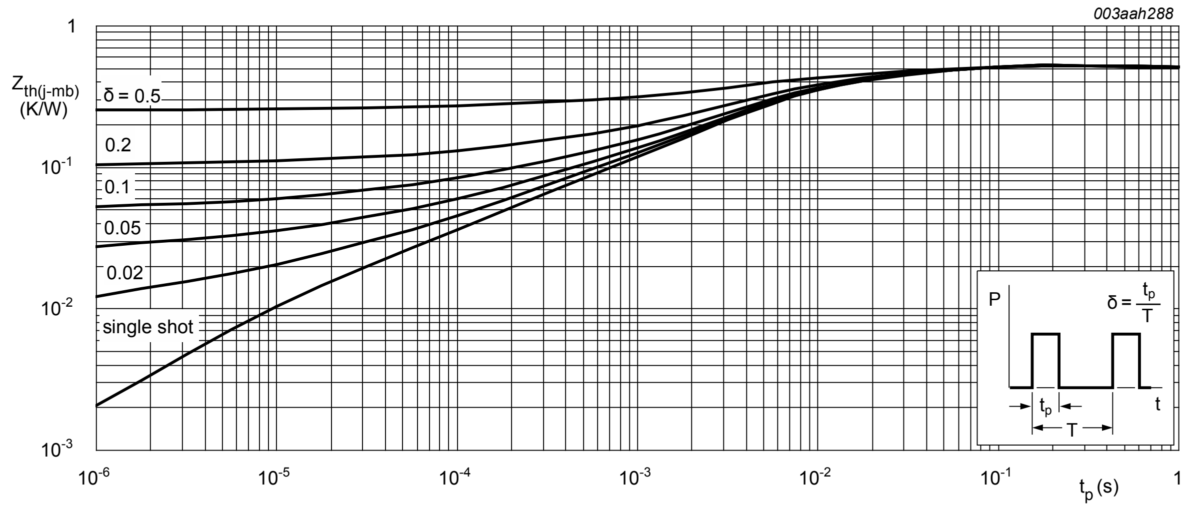


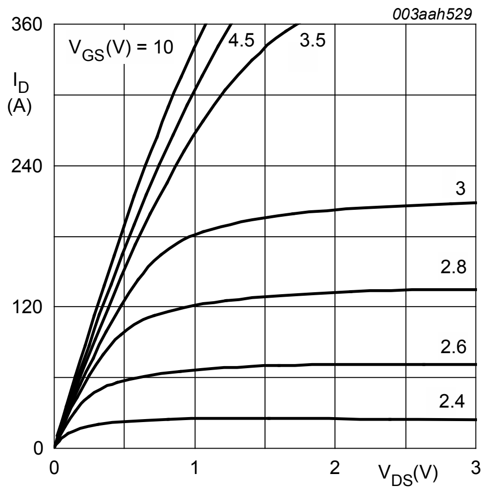
Fig. 5. Transient thermal impedance from junction to mounting base as a function of pulse duration

10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
Static characteristics							
$V_{(BR)DSS}$	drain-source breakdown voltage	I_D = 250 µA; V_{GS} = 0 V; T_j = 25 °C		60	-	-	V
		I_D = 250 µA; V_{GS} = 0 V; T_j = -55 °C		54	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	I_D = 1 mA; V_{DS} = V_{GS}; T_j = 25 °C; Fig. 9; Fig. 10		1.4	1.7	2.1	V
		I_D = 1 mA; V_{DS} = V_{GS}; T_j = -55 °C; Fig. 9		-	-	2.45	V
		I_D = 1 mA; V_{DS} = V_{GS}; T_j = 175 °C; Fig. 9		0.5	-	-	V
I_{DSS}	drain leakage current	V_{DS} = 60 V; V_{GS} = 0 V; T_j = 175 °C		-	-	500	µA
		V_{DS} = 60 V; V_{GS} = 0 V; T_j = 25 °C		-	0.09	1	µA
I_{GSS}	gate leakage current	V_{GS} = 16 V; V_{DS} = 0 V; T_j = 25 °C		-	2	100	nA
		V_{GS} = -16 V; V_{DS} = 0 V; T_j = 25 °C		-	2	100	nA
R_{DSon}	drain-source on-state resistance	V_{GS} = 4.5 V; I_D = 25 A; T_j = 25 °C; Fig. 11		-	3	3.8	mΩ
		V_{GS} = 10 V; I_D = 25 A; T_j = 25 °C; Fig. 11		-	2.7	3.4	mΩ
		V_{GS} = 10 V; I_D = 25 A; T_j = 175 °C; Fig. 12; Fig. 11		-	-	7.5	mΩ
R_G	gate resistance	f = 1 MHz		0.5	1	2	Ω

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
Dynamic characteristics							
$Q_{G(tot)}$	total gate charge	I_D = 25 A; V_{DS} = 48 V; V_{GS} = 5 V; Fig. 13; Fig. 14		-	95	-	nC
		I_D = 25 A; V_{DS} = 48 V; V_{GS} = 10 V; Fig. 13; Fig. 14		-	175	-	nC
Q_{GS}	gate-source charge			-	20	-	nC
Q_{GD}	gate-drain charge			-	31	-	nC
C_{iss}	input capacitance	V_{GS} = 0 V; V_{DS} = 25 V; f = 1 MHz; T_j = 25 °C; Fig. 15		-	10115	-	pF
C_{oss}	output capacitance			-	822	-	pF
C_{rss}	reverse transfer capacitance			-	427	-	pF
$t_{d(on)}$	turn-on delay time	V_{DS} = 45 V; R_L = 1.8 Ω; V_{GS} = 5 V; $R_{G(ext)}$ = 5 Ω		-	54.2	-	ns
t_r	rise time			-	100	-	ns
$t_{d(off)}$	turn-off delay time			-	158	-	ns
t_f	fall time			-	109	-	ns
Source-drain diode							
V_{SD}	source-drain voltage	I_S = 25 A; V_{GS} = 0 V; T_j = 25 °C; Fig. 16		-	0.78	1.2	V
t_{rr}	reverse recovery time	I_S = 20 A; dI_S/dt = -100 A/µs; V_{GS} = 0 V; V_{DS} = 25 V		-	43	-	ns
Q_r	recovered charge			-	67	-	nC



T_j = 25 °C; t_p = 300 µs

Fig. 6. Output characteristics; drain current as a function of drain-source voltage; typical values

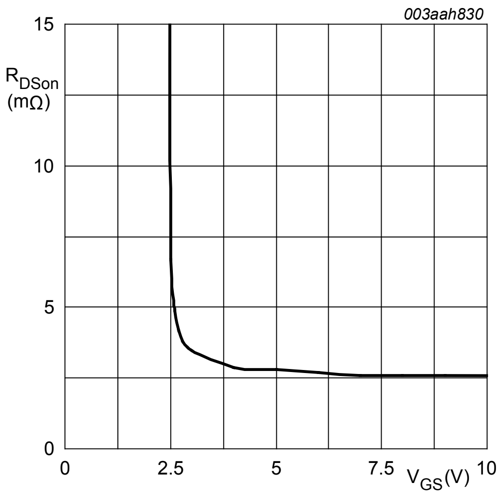


Fig. 7. Drain-source on-state resistance as a function of gate-source voltage; typical values

$T_j = 25°C;\ I_D = 25A$

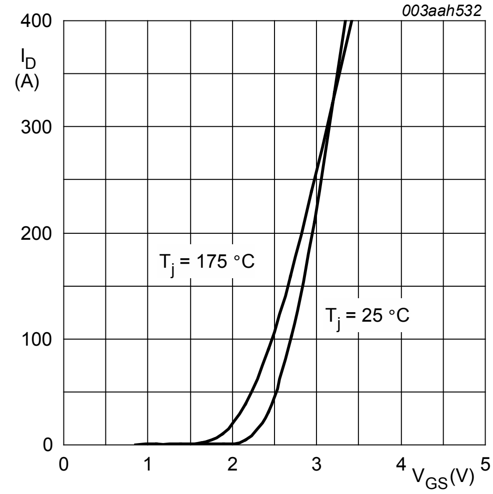


Fig. 8. Transfer characteristics; drain current as a function of gate-source voltage; typical values

$V_{DS} = 10V$

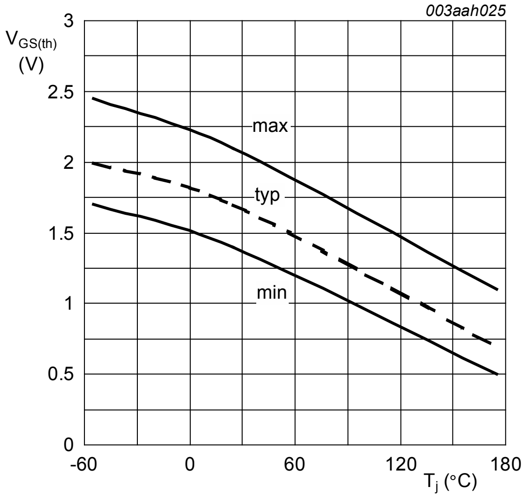


Fig. 9. Gate-source threshold voltage as a function of junction temperature

$I_D = 1$ mA; $V_{DS} = V_{GS}$

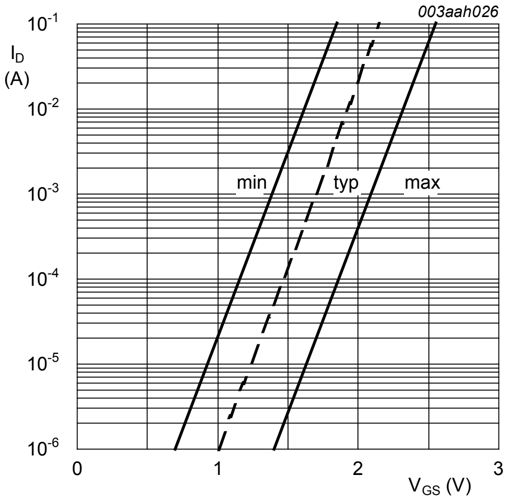
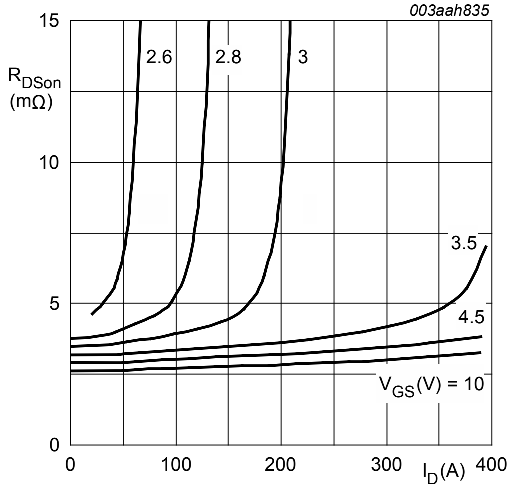


Fig. 10. Sub-threshold drain current as a function of gate-source voltage

$T_j = 25°C$; $V_{DS} = 5V$



T_j = 25 °C; t_p = 300 µs

Fig. 11. Drain-source on-state resistance as a function of drain current; typical values

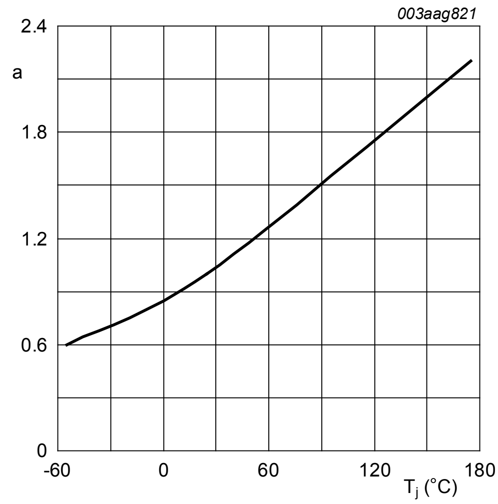


Fig. 12. Normalized drain-source on-state resistance factor as a function of junction temperature

$$a = \frac{R_{DSon}}{R_{DSon(25\,°C)}}$$

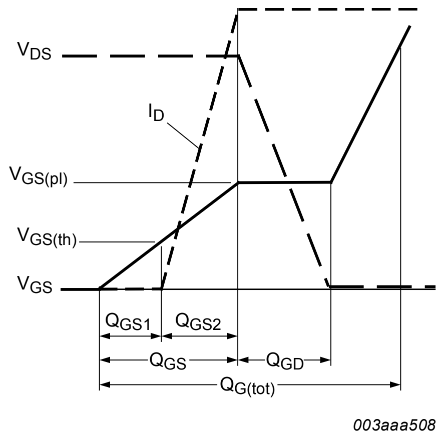


Fig. 13. Gate charge waveform definitions

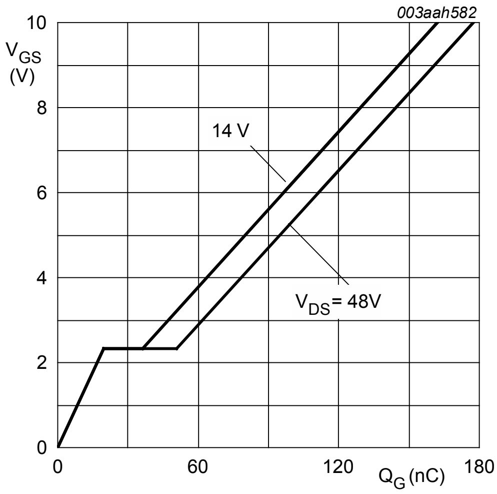


Fig. 14. Gate-source voltage as a function of gate charge; typical values

$T_j = 25°C;\ I_D = 25A$

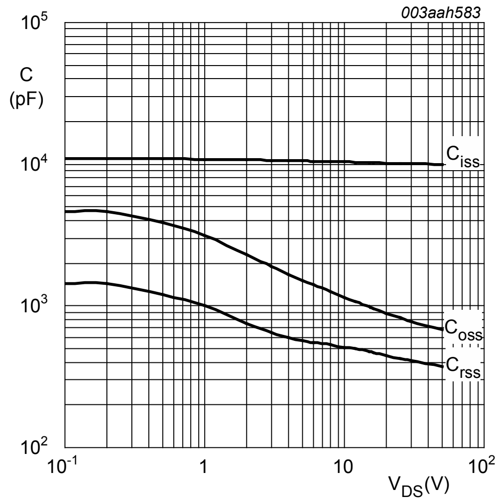


Fig. 15. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

$V_{GS} = 0V;\ f = 1MHz$

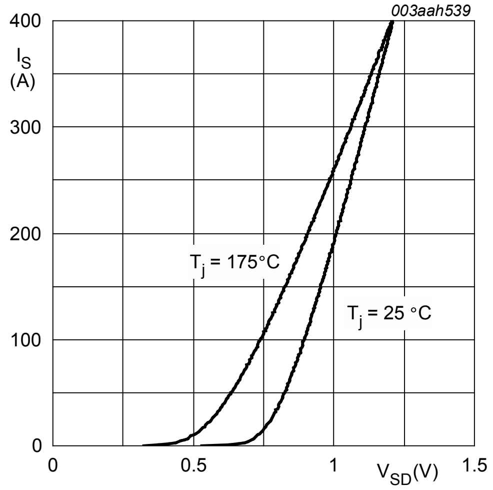
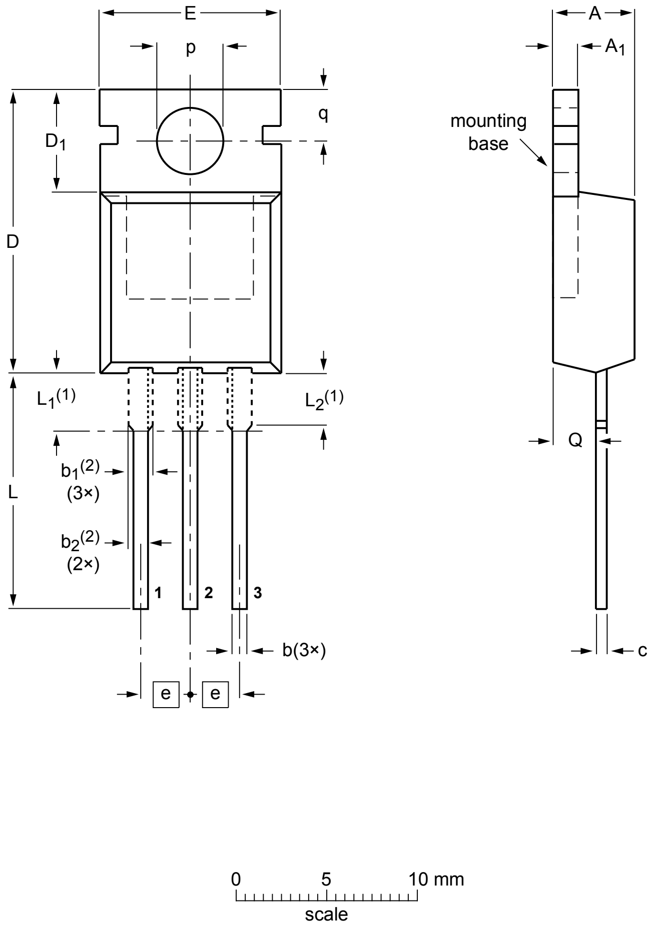


Fig. 16. Source (diode forward) current as a function of source-drain (diode forward) voltage; typical values

$V_{GS} = 0V$

11. Package outline

Plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB **SOT78**



DIMENSIONS (mm are the original dimensions)

UNIT	A	A_1	b	b_1(2)	b_2(2)	c	D	D_1	E	e	L	L_1(1)	L_2(1) max.	p	q	Q
mm	4.7 4.1	1.40 1.25	0.9 0.6	1.6 1.0	1.3 1.0	0.7 0.4	16.0 15.2	6.6 5.9	10.3 9.7	2.54	15.0 12.8	3.30 2.79	3.0	3.8 3.5	3.0 2.7	2.6 2.2

Notes

1. Lead shoulder designs may vary.
2. Dimension includes excess dambar.

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT78		3-lead TO-220AB	SC-46			~~08-04-23~~ 08-06-13

Fig. 17. Package outline TO-220AB (SOT78)

12. Legal information

12.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.
[2] The term 'short data sheet' is explained in section "Definitions".
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